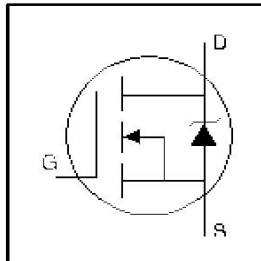


# IRFPC50LCPbF

- Ultra Low Gate Charge
- Reduced Gate Drive Requirement
- Enhanced 30V  $V_{GS}$  Rating
- Reduced  $C_{iss}$ ,  $C_{oss}$ ,  $C_{rss}$
- Isolated Central Mounting Hole
- Dynamic  $dv/dt$  Rated
- Repetitive Avalanche Rated
- Lead-Free

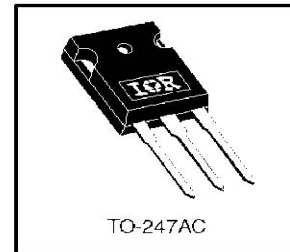


$V_{DSS} = 600V$
$R_{DS(on)} = 0.60\Omega$
$I_D = 11A$

## Description

This new series of Low Charge HEXFET Power MOSFETs achieve significantly lower gate charge over conventional MOSFETs. Utilizing advanced Hexfet technology the device improvements allow for reduced gate drive requirements, faster switching speeds and increased total system savings. These device improvements combined with the proven ruggedness and reliability of HEXFETs offer the designer a new standard in power transistors for switching applications.

The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole.




## Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	11	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10V$	7.3	
$I_{DM}$	Pulsed Drain Current ①	44	
$P_D @ T_C = 25^\circ C$	Power Dissipation	190	W
	Linear Derating Factor	1.5	W/°C
$V_{GS}$	Gate-to-Source Voltage	±30	V
$E_{AS}$	Single Pulse Avalanche Energy ②	920	mJ
$I_{AR}$	Avalanche Current ③	11	A
$E_{AR}$	Repetitive Avalanche Energy ①	19	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$ ④	3.0	V/ns
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw.	10 lbf•in (1.1N•m)	

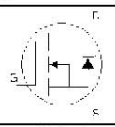
## Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.65	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	40	

## Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	600	—	—	V	$V_{GS} = 0V, I_D = 250\mu A$
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.59	—	V/°C	Reference to $25^\circ\text{C}, I_D = 1mA$
$R_{DS(ON)}$	Static Drain-to-Source On-Resistance	—	—	0.60	$\Omega$	$V_{GS} = 10V, I_D = 6.6A$ ④
$V_{GS(th)}$	Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}, I_D = 250\mu A$
$g_{fs}$	Forward Transconductance	7.0	—	—	S	$V_{DS} = 100V, I_D = 6.6A$
$I_{DSS}$	Drain-to-Source Leakage Current	—	—	25	$\mu A$	$V_{DS} = 600V, V_{GS} = 0V$
		—	—	250		$V_{DS} = 480V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
$I_{GSS}$	Gate-to-Source Forward Leakage	—	—	100	nA	$V_{GS} = 20V$
	Gate-to-Source Reverse Leakage	—	—	-100		$V_{GS} = -20V$
$Q_g$	Total Gate Charge	—	—	84	nC	$I_D = 11A$
$Q_{gs}$	Gate-to-Source Charge	—	—	18		$V_{DS} = 360V$
$Q_{gd}$	Gate-to-Drain ("Miller") Charge	—	—	36		$V_{GS} = 10V$ , See Fig. 6 and 13 ④
$t_{d(on)}$	Turn-On Delay Time	—	17	—	ns	$V_{DD} = 300V$
$t_r$	Rise Time	—	32	—		$I_D = 11A$
$t_{d(off)}$	Turn-Off Delay Time	—	41	—		$R_G = 6.2\Omega$
$t_f$	Fall Time	—	26	—		$R_D = 30\Omega$ , See Fig. 10 ④
$L_D$	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact 
$L_S$	Internal Source Inductance	—	13	—		
$C_{iss}$	Input Capacitance	—	2300	—	pF	$V_{GS} = 0V$
$C_{oss}$	Output Capacitance	—	270	—		$V_{DS} = 25V$
$C_{rss}$	Reverse Transfer Capacitance	—	28	—		$f = 1.0MHz$ , See Fig. 5

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
$I_S$	Continuous Source Current (Body Diode)	—	—	11	A	MOSFET symbol showing the integral reverse p-n junction diode. 
$I_{SM}$	Pulsed Source Current (Body Diode) ①	—	—	44		
$V_{SD}$	Diode Forward Voltage	—	—	1.4	V	$T_J = 25^\circ\text{C}, I_S = 11A, V_{GS} = 0V$ ④
$t_{rr}$	Reverse Recovery Time	—	590	890	ns	$T_J = 25^\circ\text{C}, I_F = 11A$
$Q_{rr}$	Reverse Recovery Charge	—	4.5	6.8	$\mu C$	$di/dt = 100A/\mu s$ ④
$t_{on}$	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by $L_S + L_D$ )				

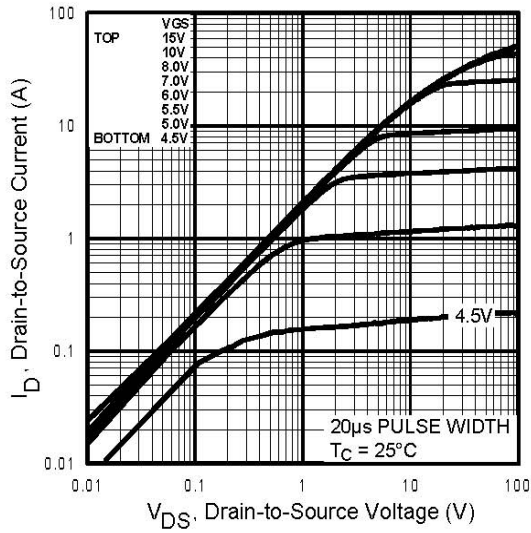
### Notes:

① Repetitive rating; pulse width limited by max. junction temperature. ( See fig. 11 )

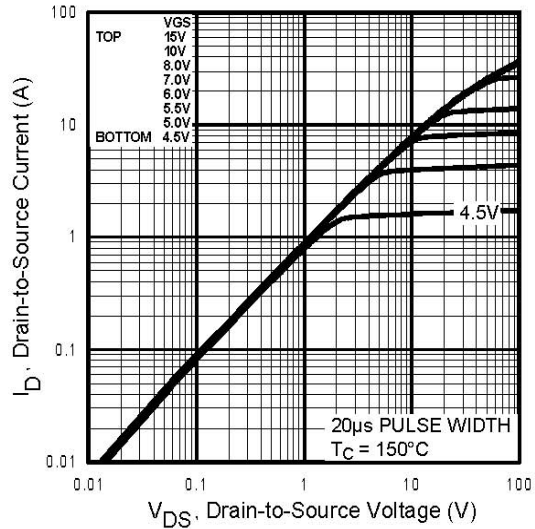
②  $I_{SD} \leq 11A, di/dt \leq 100A/\mu s, V_{DD} \leq V_{(BR)DSS}, T_J \leq 150^\circ\text{C}$

③  $V_{DD} = 25V$ , starting  $T_J = 25^\circ\text{C}$ ,  $L = 13mH$ ,  $R_G = 25\Omega, I_{AS} = 11A$ . (See Figure 12)

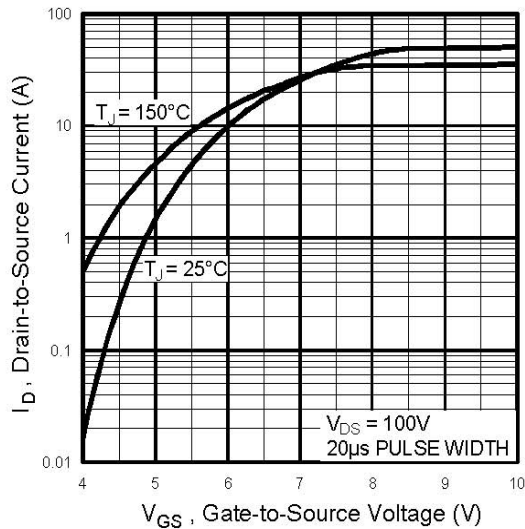
④ Pulse width  $\leq 300\mu s$ ; duty cycle  $\leq 2\%$ .



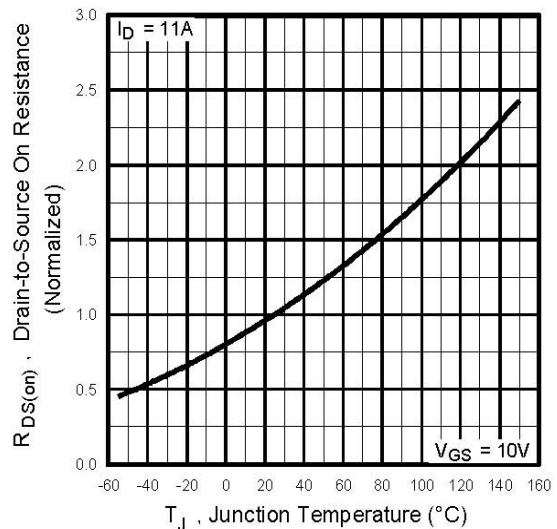
**Fig 1.** Typical Output Characteristics,  
 $T_C = 25^\circ\text{C}$



**Fig 2.** Typical Output Characteristics,  
 $T_C = 150^\circ\text{C}$

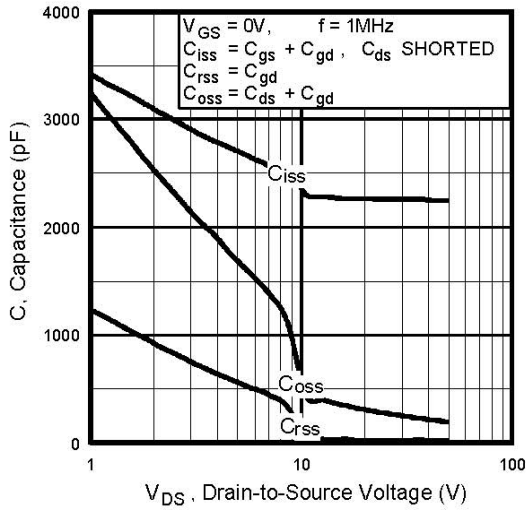


**Fig 3.** Typical Transfer Characteristics

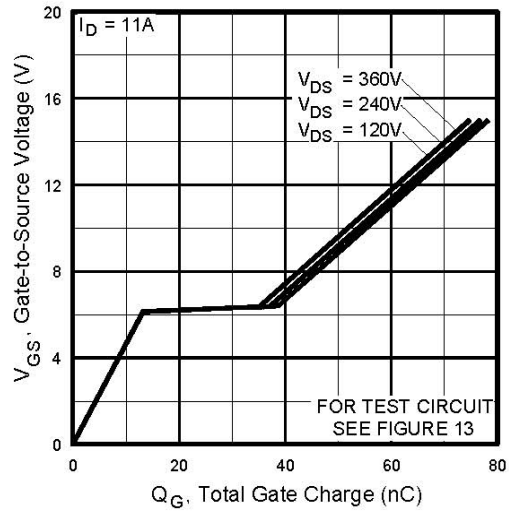


**Fig 4.** Normalized On-Resistance  
 Vs. Temperature

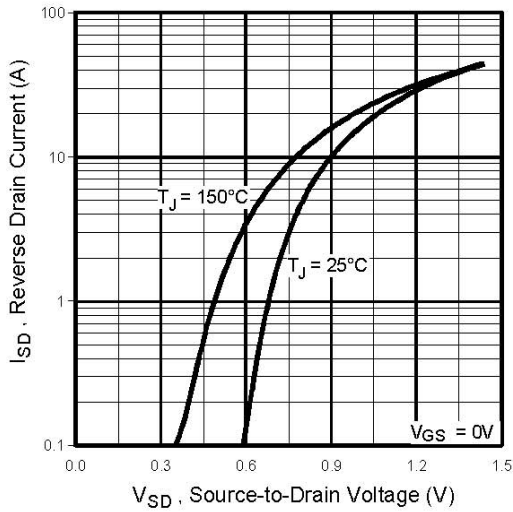
# IRFPC50LCPbF



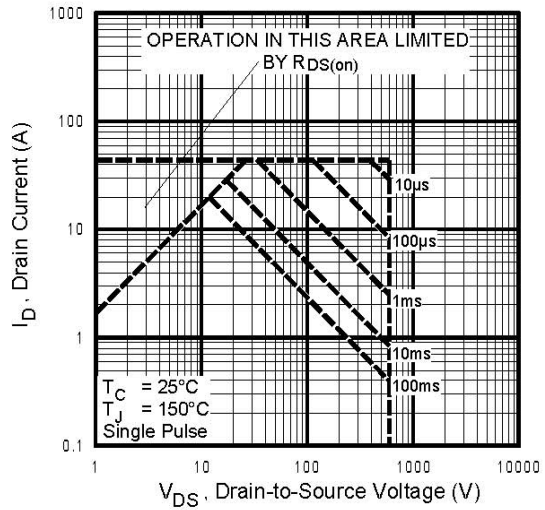
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



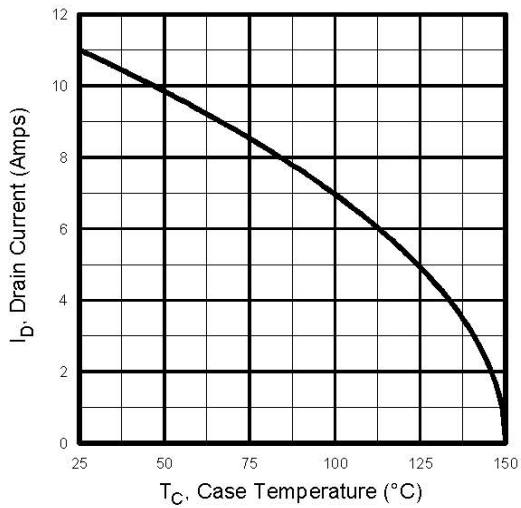
**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage



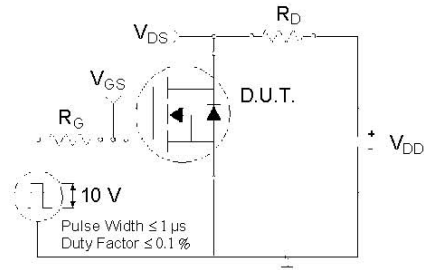
**Fig 7.** Typical Source-Drain Diode Forward Voltage



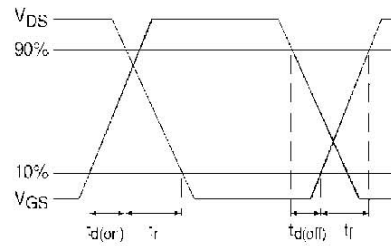
**Fig 8.** Maximum Safe Operating Area



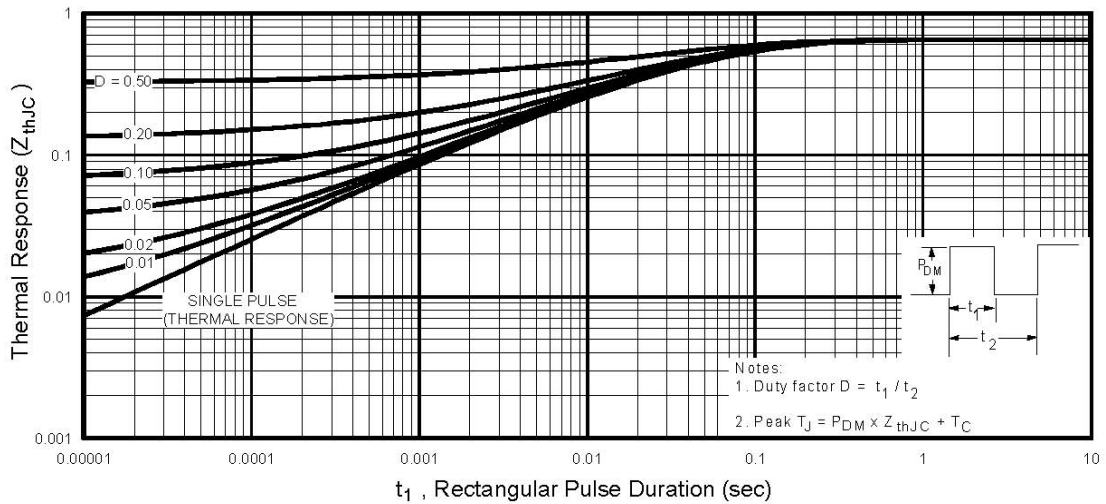
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit



**Fig 10b.** Switching Time Waveforms



**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

# IRFPC50LCPbF

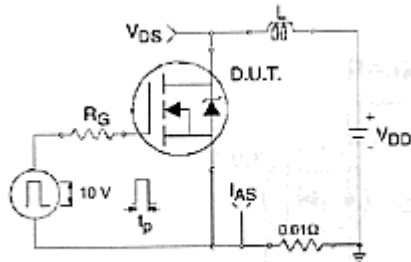


Fig 12a. Unclamped Inductive Test Circuit

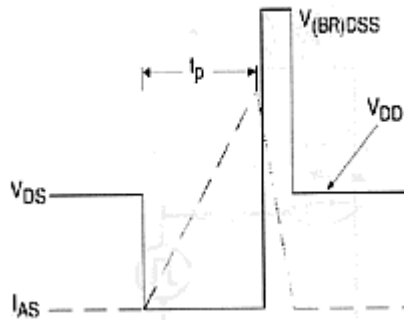


Fig 12b. Unclamped Inductive Waveforms

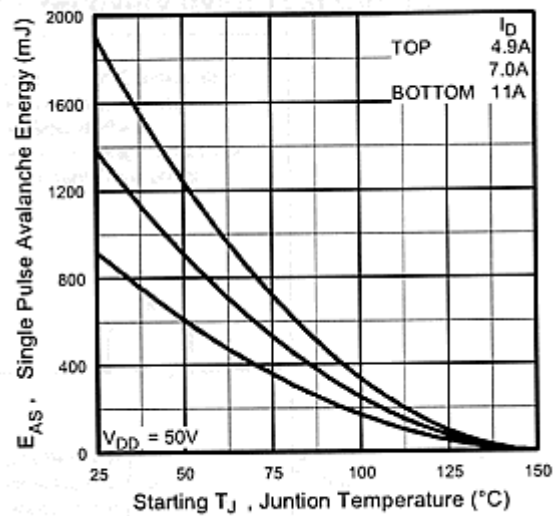


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

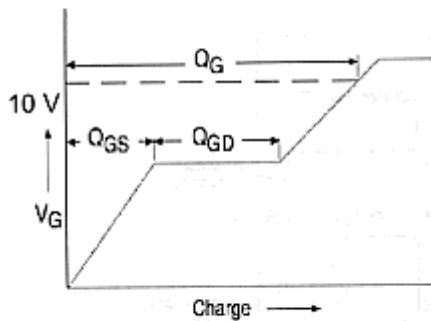


Fig 13a. Basic Gate Charge Waveform

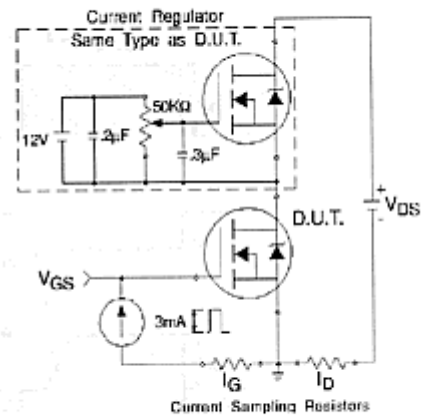
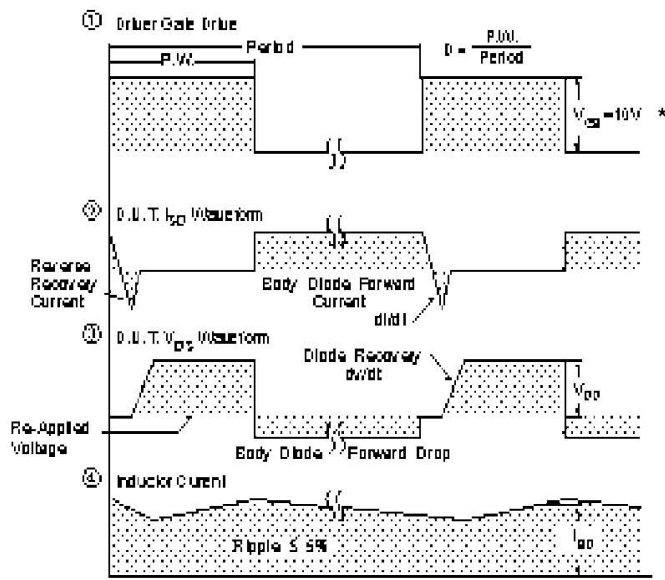
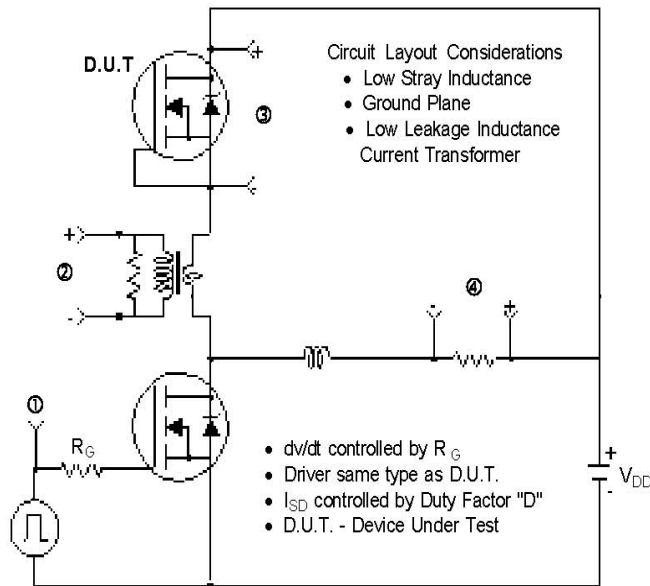


Fig 13b. Gate Charge Test Circuit



## Peak Diode Recovery dv/dt Test Circuit



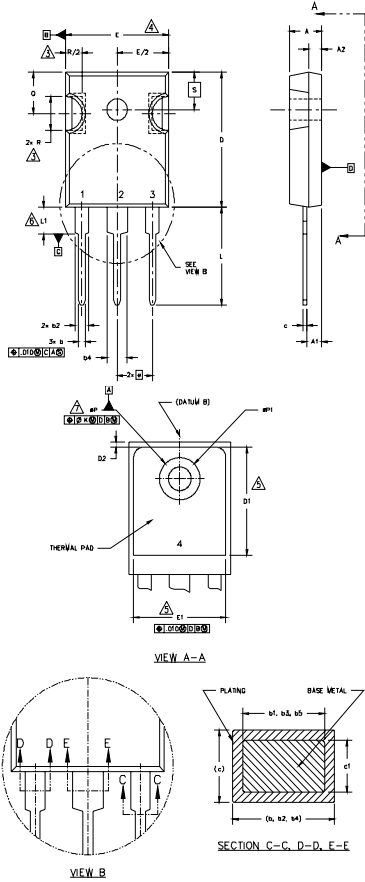
\*  $V_{GS} = 5V$  for Logic Level Devices

**Fig 14.** For N-Channel HEXFETS

# IRFP50LCPbF

International  
**IR** Rectifier

TO-247AC Package Outline Dimensions are shown in millimeters (inches)

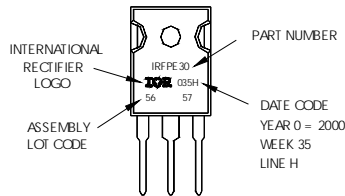


- NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
  2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
  3. CONTOUR OF SLOT OPTIONAL.
  4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
  6. LEAD FINISH UNCONTROLLED IN L1.
  7.  $\phi P$  TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91].
  8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	DIMENSIONS				NOTES	
	INCHES		MILLIMETERS			
	MIN.	MAX.	MIN.	MAX.		
A	.183	.209	4.65	5.31	<p><b>LEAD ASSIGNMENTS</b></p> <p><b>HEXFET</b></p> <p>1.- GATE 2.- DRAIN 3.- SOURCE 4.- DRAIN</p> <p><b>IGBTs, CoPACK</b></p> <p>1.- GATE 2.- COLLECTOR 3.- EMITTER 4.- COLLECTOR</p> <p><b>DIODES</b></p> <p>1.- ANODE/OPEN 2.- CATHODE 3.- ANODE</p>	
A1	.087	.102	2.21	2.59		
A2	.059	.098	1.50	2.49		
b	.039	.055	0.99	1.40		
b1	.039	.053	0.99	1.35		
b2	.065	.094	1.65	2.39		
b3	.065	.092	1.65	2.37		
b4	.102	.135	2.59	3.43		
b5	.102	.133	2.59	3.38		
c	.015	.034	0.38	0.86		
c1	.015	.030	0.38	0.76		
D	.776	.815	19.71	20.70		4
D1	.515	-	13.08	-		5
D2	.020	.030	0.51	0.76		4
E	.602	.625	15.29	15.87		
E1	.540	-	15.72	-		
e	.215 BSC		5.46 BSC			
ek	.010		2.54			
L	.559	.634	14.20	16.10		
L1	.146	.169	3.71	4.29		
N	3		7.62 BSC			
$\phi P$	.140	.144	3.56	3.66		
$\phi P1$	-	.275	-	6.98		
Q	.209	.224	5.31	5.69		
R	.178	.216	4.52	5.49		
S	.217 BSC		5.51 BSC			

## TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30 WITH ASSEMBLY LOT CODE 5667 ASSEMBLED ON VWV35, 2000 IN THE ASSEMBLY LINE "H"  
**Note:** "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.

International  
**IR** Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105

TAC Fax: (310) 252-7903

Visit us at [www.irf.com](http://www.irf.com) for sales contact information.12/04

[www.irf.com](http://www.irf.com)